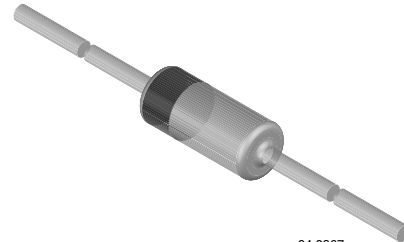


## Small Signal Fast Switching Diodes

### Features

- Silicon epitaxial planar diodes
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



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### Applications

- Extreme fast switches

### Mechanical Data

**Case:** DO35 glass case

**Weight:** approx. 125 mg

**Cathode Band Color:** black

**Packaging Codes/Options:**

TR/10 k per 13" reel (52 mm tape), 50 k/box

TAP/10 k per Ammopack (52 mm tape), 50 k/box

### Parts Table

Part	Ordering code	Type Marking	Remarks
1N4448	1N4448-TAP or 1N4448-TR	V4448	Ammopack/tape and reel

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		$V_{RRM}$	100	V
Reverse voltage		$V_R$	75	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	$I_{FSM}$	2	A
Repetitive peak forward current		$I_{FRM}$	500	mA
Forward continuous current		$I_F$	300	mA
Average forward current	$V_R = 0$	$I_{FAV}$	150	mA
Power dissipation	$l = 4\text{ mm}, T_L = 45\text{ }^{\circ}\text{C}$	$P_{tot}$	440	mW
	$l = 4\text{ mm}, T_L \leq 25\text{ }^{\circ}\text{C}$	$P_{tot}$	500	mW

### Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	$l = 4\text{ mm}, T_L = \text{constant}$	$R_{thJA}$	350	K/W
Junction temperature		$T_j$	175	$^{\circ}\text{C}$
Storage temperature range		$T_{stg}$	- 65 to + 150	$^{\circ}\text{C}$

### Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 5\text{ mA}$	$V_F$	620		720	mV
	$I_F = 100\text{ mA}$	$V_F$			1000	mV
Reverse current	$V_R = 20\text{ V}$	$I_R$			25	nA
	$V_R = 20\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	$I_R$			50	$\mu\text{A}$
	$V_R = 75\text{ V}$	$I_R$			5	$\mu\text{A}$
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$	$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0, f = 1\text{ MHz}, V_{HF} = 50\text{ mV}$	$C_D$			4	pF
Rectification efficiency	$V_{HF} = 2\text{ V}, f = 100\text{ MHz}$	$\eta_r$	45			%
Reverse recovery time	$I_F = I_R = 10\text{ mA}, i_R = 1\text{ mA}$	$t_{rr}$			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$	$t_{rr}$			4	ns

### Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

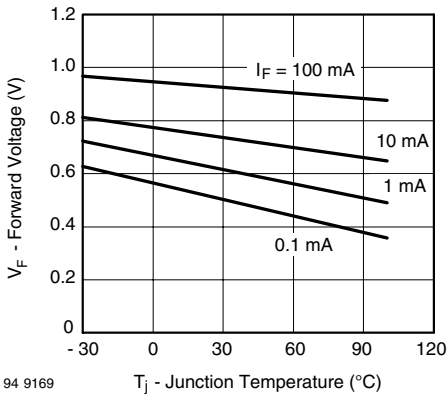


Figure 1. Forward Voltage vs. Junction Temperature

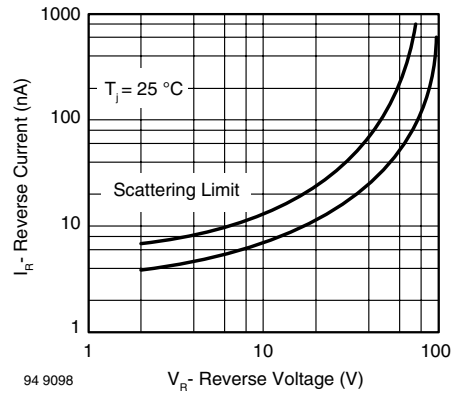


Figure 3. Reverse Current vs. Reverse Voltage

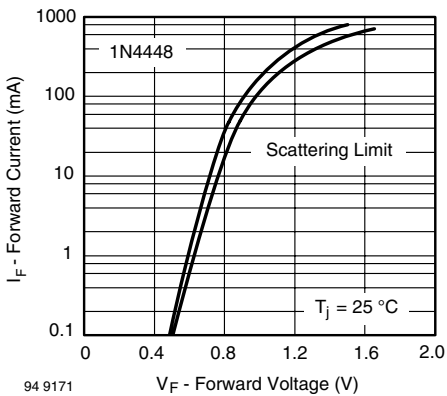


Figure 2. Forward Current vs. Forward Voltage

**Package Dimensions** in millimeters (inches): **DO35**

